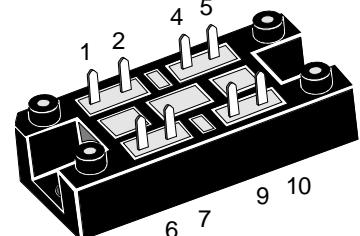
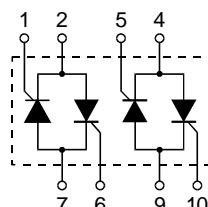


AC Controller Modules

I_{RMS} = 2x 45 A
V_{RRM} = 800-1600 V

V _{RSM} V _{DSM} V	V _{RRM} V _{DRM} V	Type
800	800	VW2x45-08io1
1200	1200	VW2x45-12io1
1400	1400	VW2x45-14io1
1600	1600	VW2x45-16io1



Symbol	Test Conditions	Maximum Ratings		
I _{RMS}	T _C = 85°C, (per phase)	45	A	
I _{TRMS}	T _{VJ} = T _{VJM}	32	A	
I _{TAVM}	T _C = 85°C; (180° sine ; per thyristor)	20	A	
I _{TSM}	T _{VJ} = 45°C; V _R = 0	300 t = 10 ms (50 Hz), sine 320 t = 8.3 ms (60 Hz), sine	A A	
	T _{VJ} = T _{VJM} V _R = 0	270 t = 10 ms (50 Hz), sine 290 t = 8.3 ms (60 Hz), sine	A A	
I ² t	T _{VJ} = 45°C V _R = 0	450 t = 10 ms (50 Hz), sine 430 t = 8.3 ms (60 Hz), sine	A ² s A ² s	
	T _{VJ} = T _{VJM} V _R = 0	360 t = 10 ms (50 Hz), sine 350 t = 8.3 ms (60 Hz), sine	A ² s A ² s	
(di/dt) _{cr}	T _{VJ} = T _{VJM} f = 50 Hz, t _p = 200 μs V _D = 2/3 V _{DRM} I _G = 0.45 A di _G /dt = 0.45 A/μs	repetitive, I _T = 45 A non repetitive, I _T = I _{TAVM}	100 500	A/μs A/μs
(dv/dt) _{cr}	T _{VJ} = T _{VJM} ; R _{GR} = ∞; method 1 (linear voltage rise)	V _{DR} = 2/3 V _{DRM}	1000	V/μs
P _{GM}	T _{VJ} = T _{VJM} I _T = I _{TAVM}	t _p = 30 μs t _p = 300 μs	10 5	W W
P _{GAVM}			0.5	W
V _{RGM}			10	V
T _{VJ}			-40...+125	°C
T _{VJM}			125	°C
T _{stg}			-40...+125	°C
V _{ISOL}	50/60 Hz, RMS I _{ISOL} ≤ 1 mA	t = 1 min t = 1 s	3000 3600	V~ V~
M _d	Mounting torque (M5)		2-2.5/18-22	Nm/lb.in.
Weight	typ.	35	g	

Data according to IEC 60747 refer to a single thyristor/diode unless otherwise stated.
 IXYS reserves the right to change limits, test conditions and dimensions

Symbol	Test Conditions	Characteristic Values		
I_D, I_R	$T_{VJ} = T_{VJM}$; $V_R = V_{RRM}$; $V_D = V_{DRM}$	\leq	5	mA
V_T	$I_T = 45 \text{ A}$; $T_{VJ} = 25^\circ\text{C}$	\leq	1.52	V
V_{TO}	For power-loss calculations only	0.85		V
r_T		15		$\text{m}\Omega$
V_{GT}	$V_D = 6 \text{ V}$; $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = -40^\circ\text{C}$	\leq	1.5	V
I_{GT}	$V_D = 6 \text{ V}$; $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = -40^\circ\text{C}$	\leq	100	mA
V_{GD}	$T_{VJ} = T_{VJM}$;	\leq	0.2	V
I_{GD}	$V_D = 2/3 V_{DRM}$	\leq	5	mA
I_L	$T_{VJ} = 25^\circ\text{C}$; $t_p = 10 \mu\text{s}$ $I_G = 0.45 \text{ A}$; $di_G/dt = 0.45 \text{ A}/\mu\text{s}$	\leq	450	mA
I_H	$T_{VJ} = 25^\circ\text{C}$; $V_D = 6 \text{ V}$; $R_{GK} = \infty$	\leq	200	mA
t_{gd}	$T_{VJ} = 25^\circ\text{C}$; $V_D = 1/2 V_{DRM}$ $I_G = 0.45 \text{ A}$; $di_G/dt = 0.45 \text{ A}/\mu\text{s}$	\leq	2	μs
t_q	$T_{VJ} = T_{VJM}$; $I_T = 20 \text{ A}$, $t_p = 200 \mu\text{s}$; $di/dt = -10 \text{ A}/\mu\text{s}$ $V_R = 100 \text{ V}$; $dv/dt = 15 \text{ V}/\mu\text{s}$; $V_D = 2/3 V_{DRM}$	typ.	150	μs
R_{thJC}	per thyristor; DC		1.25	K/W
	per module		0.31	K/W
R_{thJK}	per thyristor; DC		1.55	K/W
	per module		0.39	K/W
d_s	Creeping distance on surface		12.7	mm
d_A	Creepage distance in air		9.4	mm
a	Max. allowable acceleration		50	m/s^2

Dimensions in mm (1 mm = 0.0394")

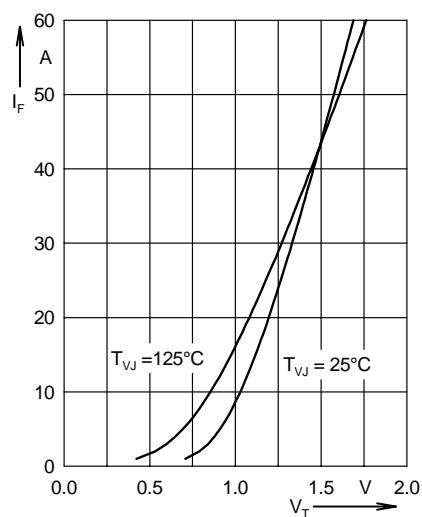
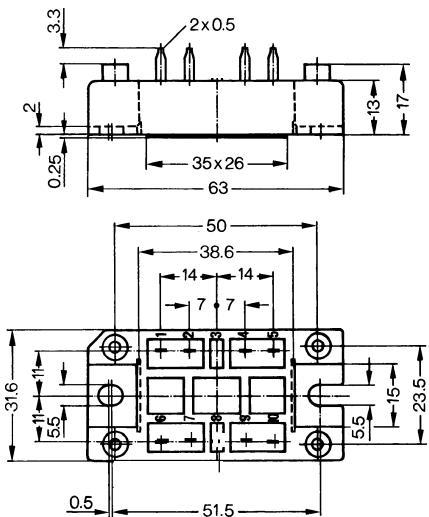


Fig. 3 Forward current versus voltage drop per leg

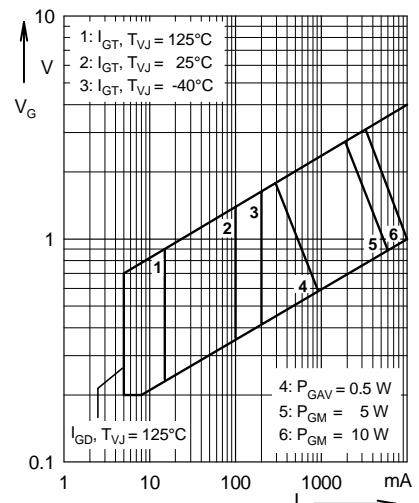


Fig. 1 Gate trigger characteristics

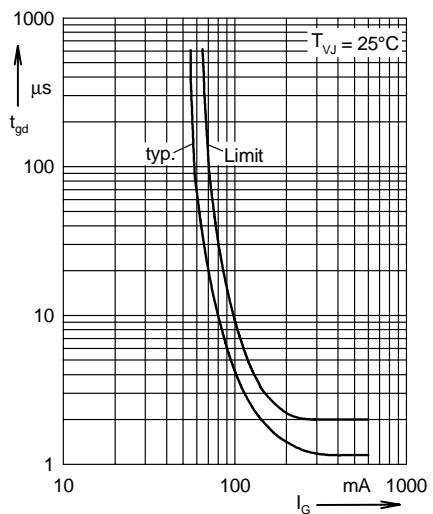


Fig. 2 Gate trigger delay time

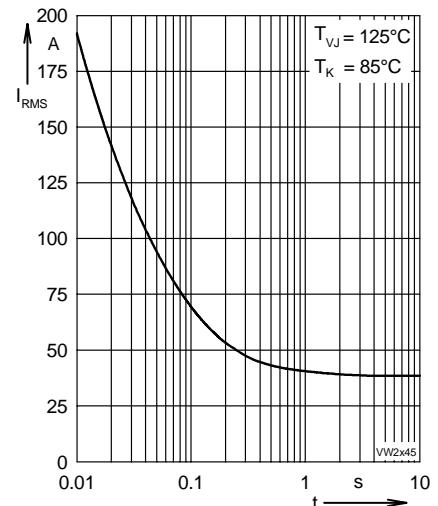


Fig. 4 Rated RMS current versus time (360° conduction)

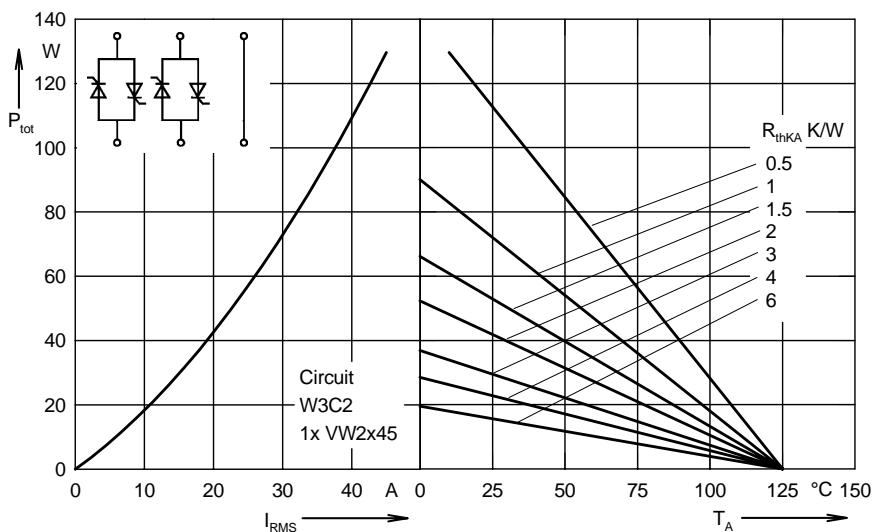


Fig. 5 Load current capability for two phase AC controller

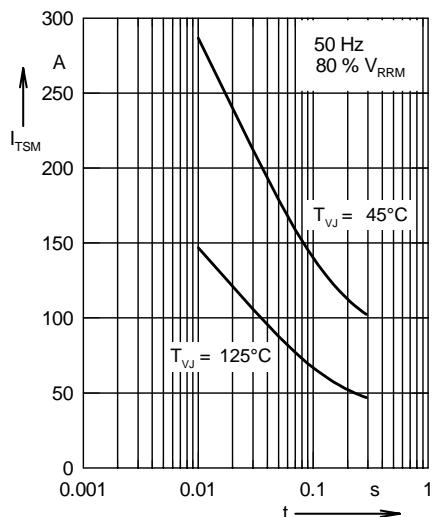


Fig. 6 Surge overload current

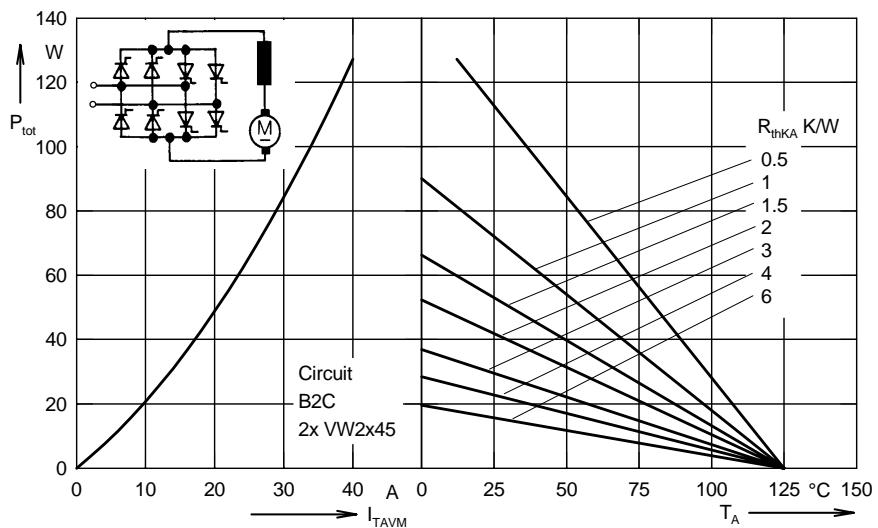


Fig. 7 Power dissipation versus direct output current and ambient temperature cyclo converter, four quadrant operation

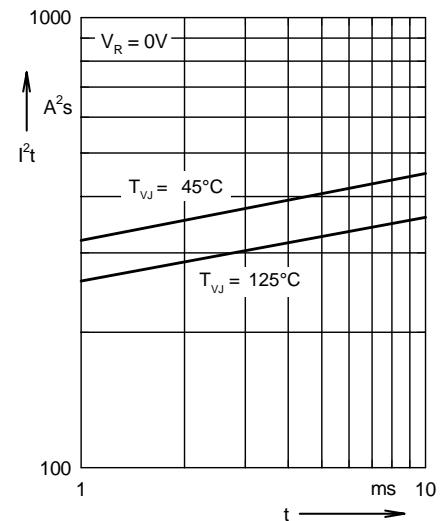


Fig. 8 I^2t versus time (per thyristor)

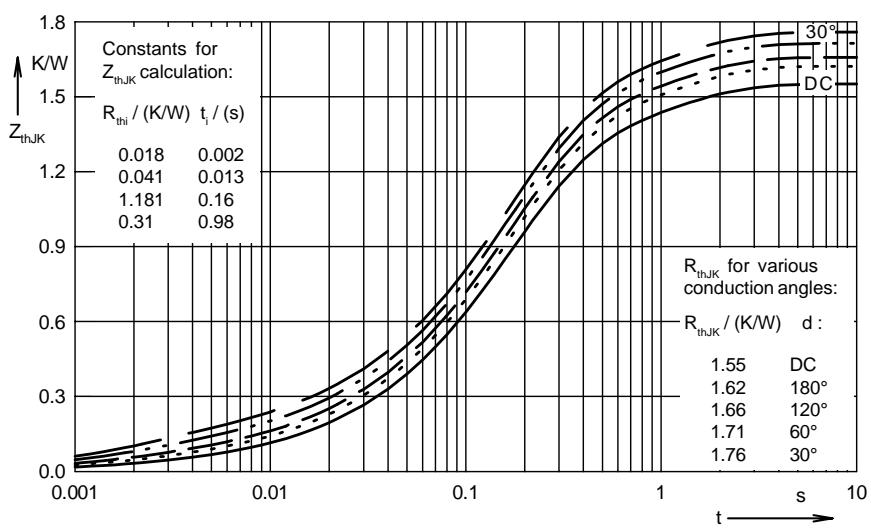


Fig. 9 Transient thermal impedance junction to heatsink (per thyristor)

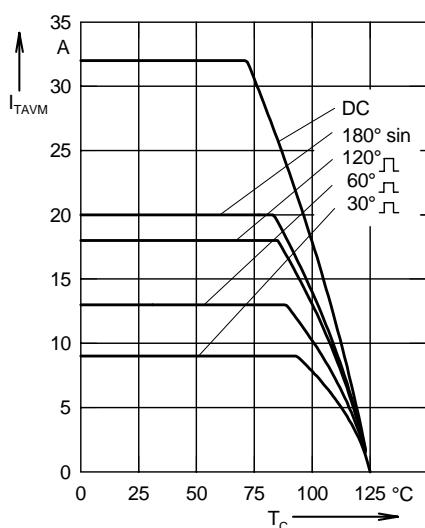


Fig. 10 Maximum forward current at case temperature